

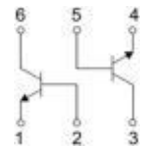
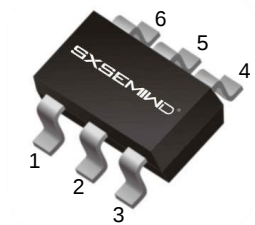
FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	65	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current –Continuous	0.1	A
P_C	Collector Dissipation	200	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

SOT-363

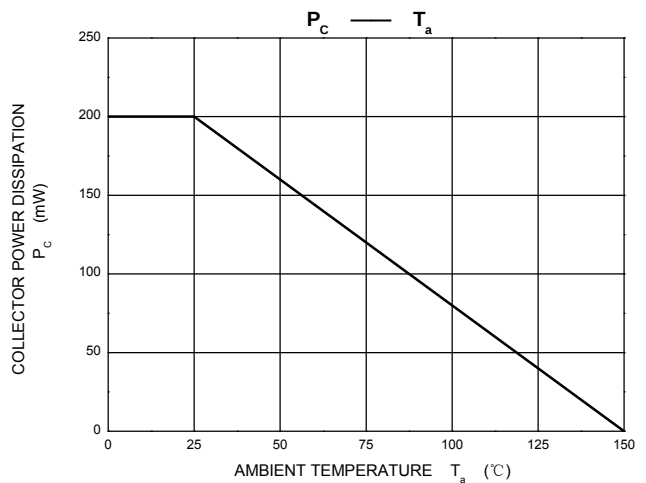
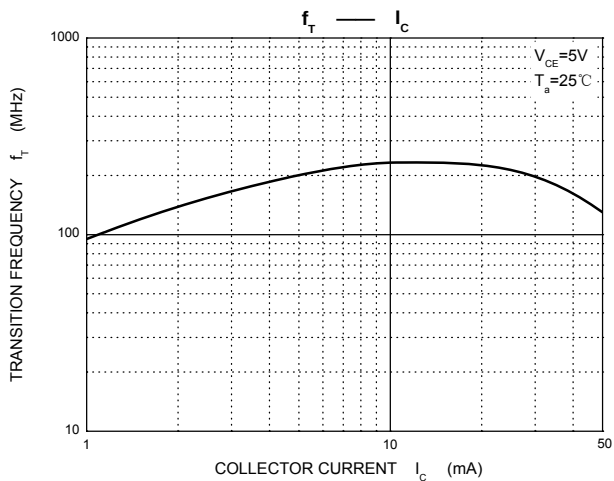
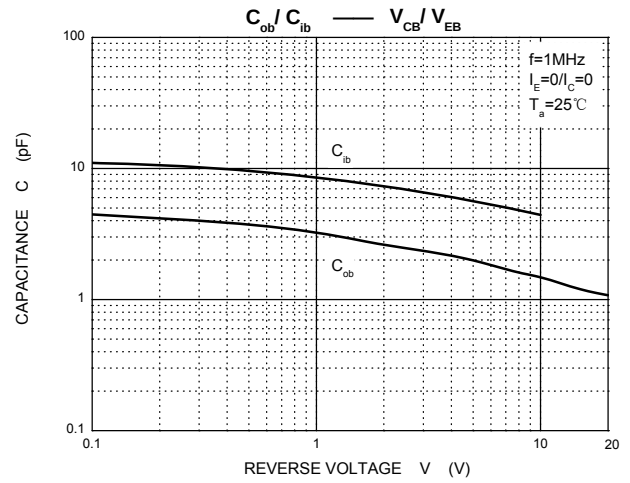
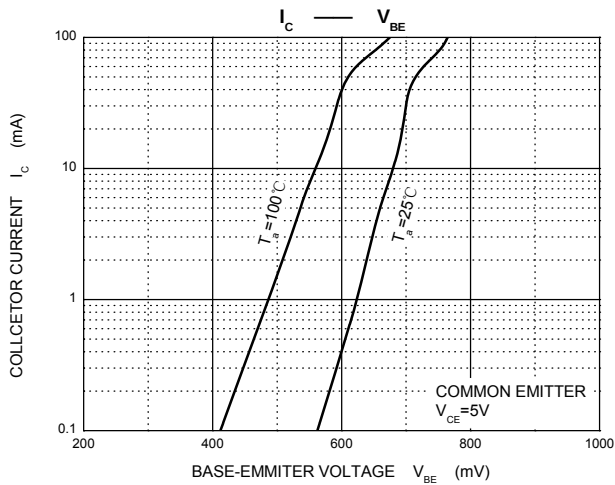
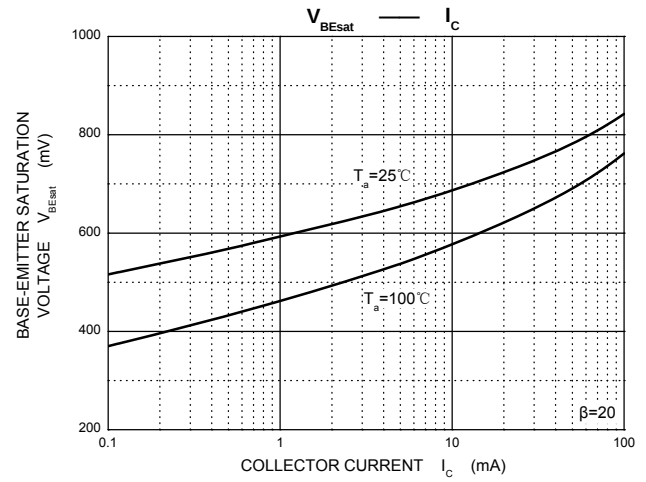
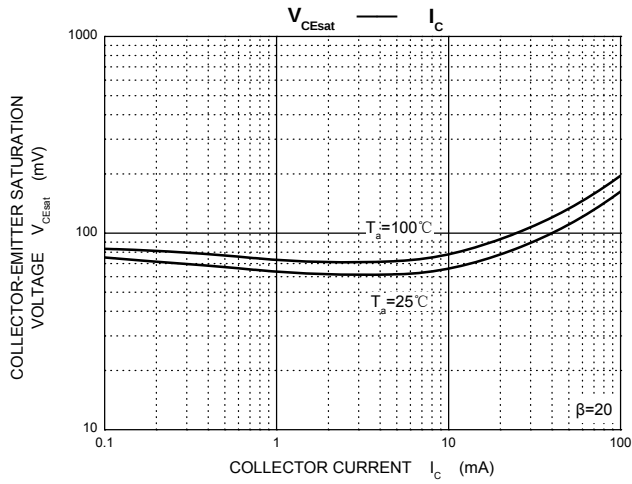
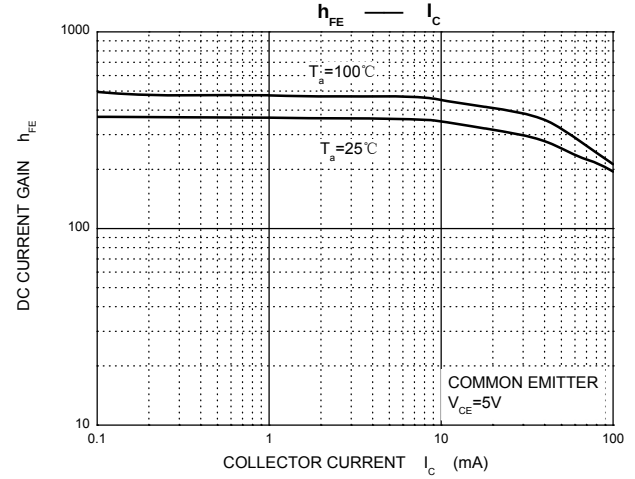
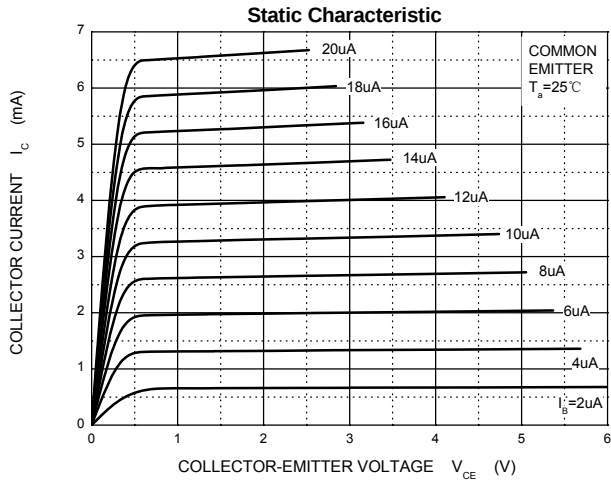


MARKING: 4Ft

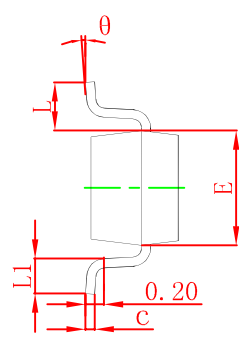
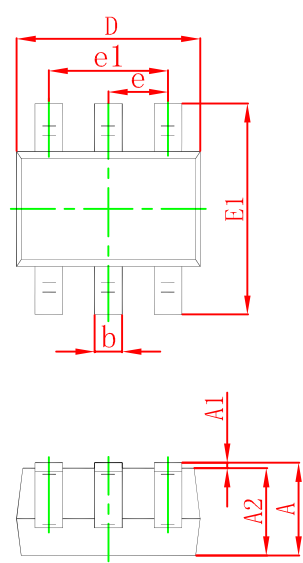
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	65			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 30\text{V}, I_E = 0$			15	nA
Emitter cut-off current	I_{EBO}	$I_C = 0, V_{EB} = 5\text{V}$			500	nA
DC current gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	200		450	
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$			0.1	V
	$V_{CE(sat)(2)}$	$I_C = 100\text{mA}, I_B = 5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$		0.77		V
Transition frequency	f_T	$V_{CB} = 5\text{V}, I_E = 10\text{mA}, f = 100\text{MHz}$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$			1.5	pF

Typical Characteristics

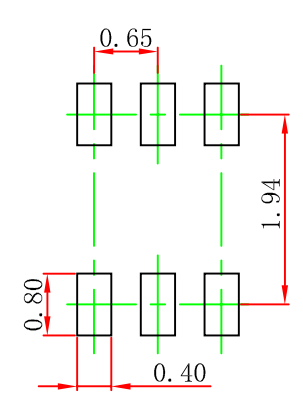


SOT-363 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-363 Suggested Pad Layout



Note:
1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05mm.
3. The pad layout is for reference purposes only.